



#### HALF-BRIDGE GATE DRIVER IN SO-8

### **Description**

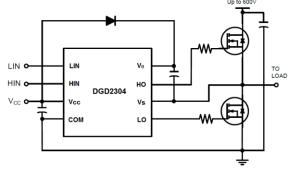
The DGD2304 is a high voltage / high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. High voltage processing techniques enable the DGD2304's high side to switch to 600V in a bootstrap operation.

The DGD2304 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. An internal deadtime of 100ns protects high-voltage MOSFETs from shoot-through.

The DGD2304 is offered in the SO-8 package and operates over an extended -40°C to +125°C temperature range.

### **Applications**

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers



**Typical Configuration** 

#### **Features**

- Floating High-Side Driver In Bootstrap Operation to 600V
- Drives Two N-channel MOSFETs or IGBTs in a Half Bridge Configuration
- 290mA Source/600mA Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Logic and Dead Time (100ns) to Protect MOSFETs
- Logic Input (HIN and LIN) 3.3V Capability
- Schmitt Triggered Logic Inputs with Internal Pull Down
- Undervoltage Lockout for High and Low Side Drivers
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.075 grams (Approximate)



### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD2304S8-13	DGD2304	13	12	2,500

Notes: 1. No purpo

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

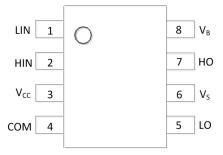
### **Marking Information**



);; = Manufacturer's marking
DGD2304 = Product Type Marking Code
YY = Year (ex: 19 = 2019)
WW = Week (01 to 53)



### **Pin Diagrams**

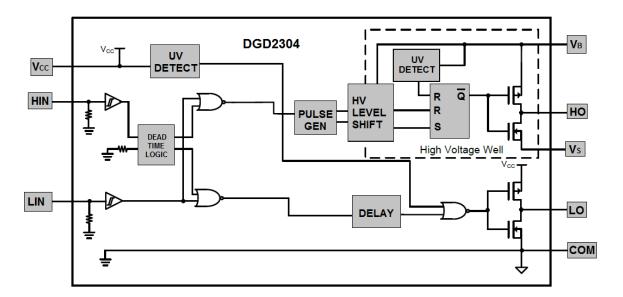


Top View: SO-8

### **Pin Descriptions**

Pin Number	Pin Name	Function
1	LIN	Logic input for Low-Side Gate Driver Output in Phase with LO
2	HIN	Logic Input for High-Side Gate Driver Output in Phase with HO
3	Vcc	Low Side and Logic Fixed Supply
4	COM	Low-Side and Logic Return
5	LO	Low-Side Gate Drive Output
6	Vs	High-Side Floating Supply Return
7	НО	High-Side Gate Drive Output
8	V <sub>B</sub>	High-Side Floating Supply

# **Functional Block Diagram**





### **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V <sub>B</sub>	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	Vs	V <sub>B</sub> -24 to V <sub>B</sub> +0.3	V
High-Side Floating Output Voltage	V <sub>HO</sub>	V <sub>S</sub> -0.3 to V <sub>B</sub> +0.3	V
Offset Supply Voltage Transient	dV <sub>S</sub> / dt	50	V/ns
Low-Side and Logic Fixed Supply Voltage	Vcc	-0.3 to +24	V
Low-Side Output Voltage	$V_{LO}$	-0.3 to V <sub>CC</sub> +0.3	V
Logic Input Voltage (HIN and LIN)	V <sub>IN</sub>	V <sub>SS</sub> -0.3 to V <sub>CC</sub> +0.3	V

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear derating factor (Note 5)	P <sub>D</sub>	1.25	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	55	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	T <sub>L</sub>	+300	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

# **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply Absolute Voltage	V <sub>B</sub>	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
High-Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High-Side Floating Output Voltage	V <sub>HO</sub>	Vs	V <sub>B</sub>	V
Low-Side and Logic Fixed Supply Voltage	V <sub>CC</sub>	10	20	V
Low-Side Output Voltage	$V_{LO}$	0	Vcc	V
Logic Input Voltage	V <sub>IN</sub>	0	5	V
Ambient Temperature	T <sub>A</sub>	-40	+125	°C

Note: 6. Logic operation for Vs of -5V to +600V.



# $\textbf{DC Electrical Characteristics} \ (V_{BIAS} \ (V_{CC}, \ V_{BS}) = 15V, \ @T_A = +25^{\circ}C, \ unless \ otherwise \ specified.) \ (Note \ 7)$

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" Input Voltage (Note 8)	V <sub>IH</sub>	2.3	_	_	V	V <sub>CC</sub> = 10V to 20V
Logic "0" Input Voltage (Note 8)	$V_{IL}$	_	_	0.7	V	V <sub>CC</sub> = 10V to 20V
High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	$V_{OH}$	_	0.05	0.2	V	$I_O = 2mA$
Low Level Output Voltage, Vo	$V_{OL}$	_	0.02	0.1	V	$I_0 = 2mA$
Offset Supply Leakage Current	$I_{LK}$	_	_	50	μA	$V_B = V_S = 600V$
Quiescent V <sub>BS</sub> Supply Current	$I_{BSQ}$	20	60	150	μΑ	$V_{IN} = 0V \text{ or } 5V$
Quiescent V <sub>CC</sub> Supply Current	Iccq	50	260	400	μΑ	$V_{IN} = 0V \text{ or } 5V$
Logic "1" Input Bias Current	I <sub>IN+</sub>	_	5.0	40	μA	$V_{IN} = 5V$
Logic "0" Input Bias Current	I <sub>IN-</sub>	_	1.0	5.0	μΑ	$V_{IN} = 0V$
V <sub>BS</sub> Supply Under-Voltage Positive Going Threshold	$V_{BSUV+}$	7.7	8.7	9.7	V	_
V <sub>BS</sub> Supply Under-Voltage Negative Going Threshold	V <sub>BSUV</sub> -	7.0	8.0	9.0	V	_
V <sub>CC</sub> Supply Under-Voltage Positive Going Threshold	V <sub>CCUV+</sub>	7.7	8.7	9.7	V	_
V <sub>CC</sub> Supply Under-Voltage Negative Going Threshold	V <sub>CCUV</sub> -	7.0	8.0	9.0	V	_
Output High Short Circuit Pulsed Current	I <sub>O+</sub>	60	290	_	mA	$V_O = 0V$ , $P_W \le 10\mu s$
Output Low Short Circuit Pulsed Current	I <sub>O-</sub>	130	600	_	mA	V <sub>O</sub> = 15V, P <sub>W</sub> ≤ 10μs

Notes:

# AC Electrical Characteristics ( $V_{BIAS}$ ( $V_{CC}$ , $V_{BS}$ ) = 15V, $C_L$ = 1000pF, @ $T_A$ = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-On Propagation Delay	t <sub>ON</sub>	_	95	210	ns	$V_S = 0V$
Turn-Off Propagation Delay	toff	_	100	210	ns	V <sub>S</sub> = 0V or 600V
Delay Matching, HO and LO Turn-On / Turn-Off	t <sub>DM ON</sub>	_	_	50	ns	_
Turn-On Rise Time	t <sub>R</sub>	_	70	120	ns	_
Turn-Off Fall Time	t <sub>F</sub>	_	35	60	ns	_
Deadtime: t <sub>DT LO-HO</sub> and t <sub>DT HO-LO</sub>	t <sub>DT</sub>	80	100	190	ns	_

<sup>7.</sup> The V<sub>IN</sub> and I<sub>IN</sub> parameters are referenced to COM and are applicable to the two logic pins: HIN and LIN. The V<sub>O</sub> and I<sub>O</sub> parameters are referenced to

<sup>......</sup> VIIN and IIN Parameters are referenced to COM and are applicable to the two logic pins: HIN and LIN. The V<sub>O</sub> and I<sub>O</sub> parameters are referenced to COM and are applicable to the respective output pins: HO and LO.

8. For optimal operation, it is recommended that the input pulses (HIN and LIN) should have an minimum amplitude of 2.3V wiith a minimum pulse width of 200ns.



### **Timing Waveforms**

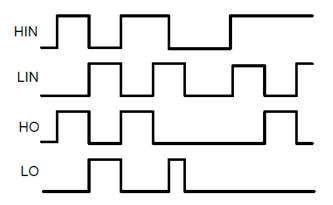


Figure 1. Input / Output Timing Diagram

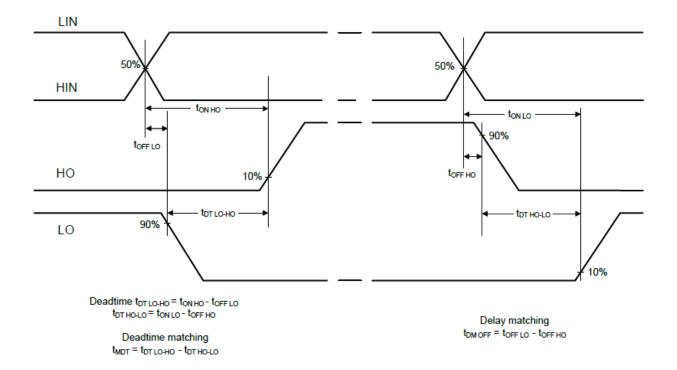


Figure 2. Switching Time Waveform Definition



# Typical Performance Characteristics (V<sub>CC</sub> = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.)

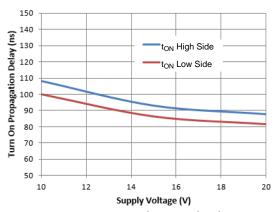


Figure 3. Turn-on Propagation Delay vs. Supply Voltage

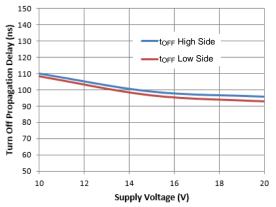


Figure 5. Turn-off Propagation Delay vs. Supply Voltage

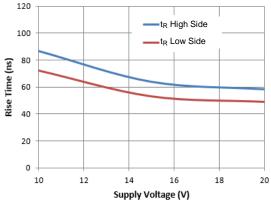


Figure 7. Rise Time vs. Supply Voltage

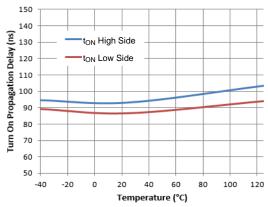


Figure 4. Turn-on Propagation Delay vs. Temperature

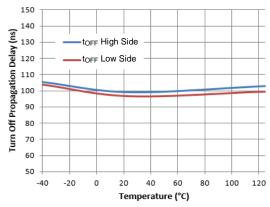


Figure 6. Turn-off Propagation Delay vs. Temperature

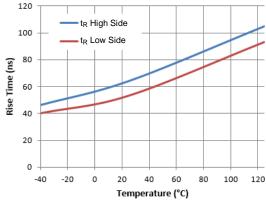


Figure 8. Rise Time vs. Temperature



# **Typical Performance Characteristics** (continued)

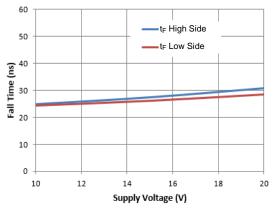
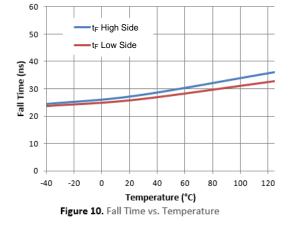


Figure 9. Fall Time vs. Supply Voltage



500 450 400 -I<sub>CCQ</sub> Quiescent Current (µA) 350 300 250 200 150 100 50 10 12 14 16 18 20

Figure 11. Quiescent Current vs. Supply Voltage

Supply Voltage (V)

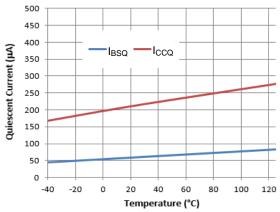


Figure 12. Quiescent Current vs. Temperature

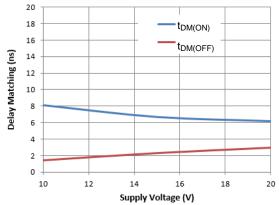


Figure 13. Delay Matching vs. Supply Voltage

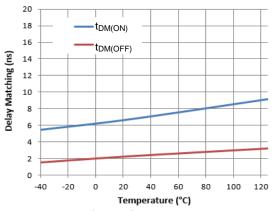


Figure 14. Delay Matching vs. Temperature



# **Typical Performance Characteristics** (continued)

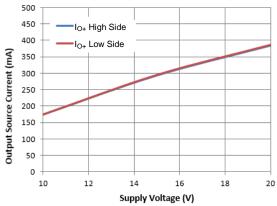


Figure 15. Output Source Current vs. Supply Voltage

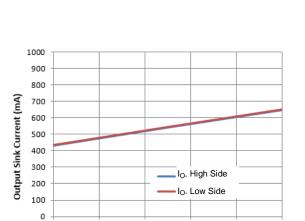


Figure 17. Output Sink Current vs. Supply Voltage

16

Supply Voltage (V)

18

20

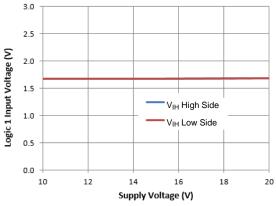


Figure 19. Logic 1 Input Voltage vs. Supply Voltage

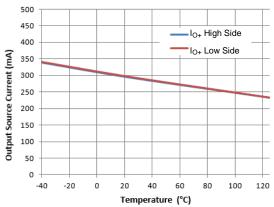


Figure 16. Output Source Current vs. Temperature

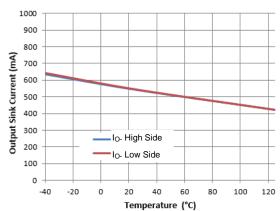


Figure 18. Output Sink Current vs. Temperature

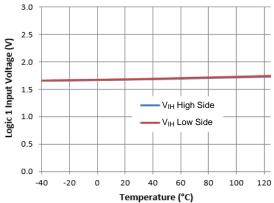


Figure 20. Logic 1 Input Voltage vs. Temperature

10



# **Typical Performance Characteristics** (continued)

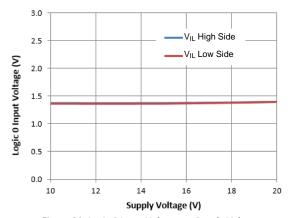


Figure 21. Logic 0 Input Voltage vs. Supply Voltage

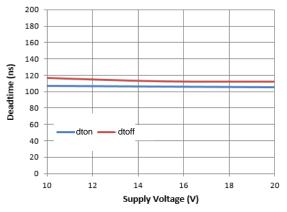


Figure 23. Deadtime vs. Supply Voltage

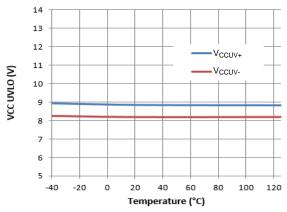


Figure 25. VCC UVLO vs. Temperature

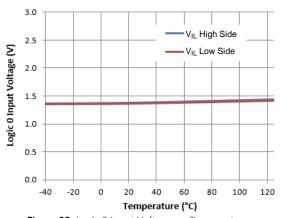


Figure 22. Logic 0 Input Voltage vs. Temperature

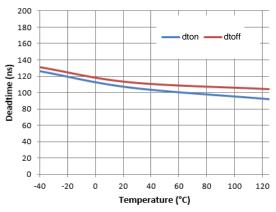


Figure 24. Deadtime vs. Temperature

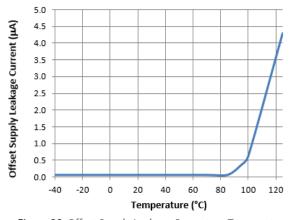
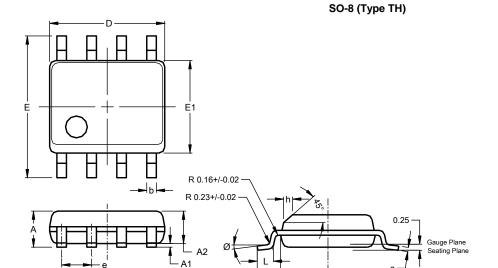


Figure 26. Offset Supply Leakage Current vs. Temperature



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

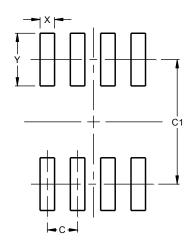


SO-8 (Type TH)					
Dim	Min	Max	Тур		
Α	1.35	1.75			
A1	0.10	0.25			
A2			1.45		
b	0.35	0.51			
С	0.190	0.248			
D	4.80	5.00	4.90		
Е	5.80	6.20	6.00		
E1	3.80	4.00	3.90		
е			1.27		
h	0.25	0.50			
L	0.41	1.27			
L1			1.04		
Ø	0°	8°			
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SO-8 (Type TH)



Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
Υ	2.20

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



#### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com

11 of 11 DGD2304 September 2019 Document Number DS38409 Rev. 3 - 2 © Diodes Incorporated

# 单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))